

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
1	BRS	L1	23	niwayama near masahiko.in.	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_TDB	2004/08/01 16:46	
2	BRS	L2	695	yoneda near kenji.in.	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_TDB	2004/08/01 16:46	
3	BRS	L3	1495	438/14.ccls.	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_TDB	2004/08/01 16:47	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
4	BRS	L4	57	3 and (substrate or wafer) near25 (infrared)	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/08/01 16:54	
5	BRS	L5	120	3 and (substrate or wafer) near25 (dopant)	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/08/01 17:01	
6	BRS	L6	388	(substrate or wafer) near25 (dopant) near25 (irradiat\$3 or radiat\$3)	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/08/01 19:18	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
7	BRS	L7	57	(substrate or wafer) near25 (dopant) near25 (temperature) near15 (irradiat\$3 or radiat\$3)	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/08/01 17:02	
8	BRS	L8	18	(substrate or wafer) near25 (dopant) near25 (irradiat\$3 or radiat\$3) near15 (absorb\$3)	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/08/01 17:14	
9	BRS	L9	189068	(temperature) near25 (substrate)	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/08/01 17:41	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
10	BRS	L10	5284	(temperature) near25 (substrate) near15 (radiat\$3 or infrared)	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_TDB	2004/08/01 17:42	
11	BRS	L11	835	(temperature) near25 (substrate or wafer) near15 (radiat\$3 or infrared) near25 (detect\$3)	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_TDB	2004/08/01 17:44	
12	BRS	L12	393	(temperature) near25 (substrate or wafer) near15 (radiat\$3 or infrared) near25 (intensity)	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_TDB	2004/08/01 17:58	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
13	BRS	L13	15083	(stabiliz\$3) near15 (wafer or substrate)	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/08/01 18:00	
14	BRS	L14	1989	(stabiliz\$3) near15 (wafer or substrate) near15 (temperature)	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/08/01 18:00	
15	BRS	L15	102	(stabiliz\$3) near15 (wafer or substrate) near15 (temperature) near15 (maintain\$3)	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/08/01 18:01	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
16	BRS	L16	2686	(semiconductor near3 layer) near5 (dopant)	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_TDB	2004/08/01 19:19	
17	BRS	L17	3	(semiconductor near3 layer) near5 (dopant) near15 (radiat\$3 or infrared or if) near15 (substrate or wafer)	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_TDB	2004/08/01 19:21	
18	BRS	L18	10404	(semiconductor or dopant near3 layer) near15 (radiat\$3 or infrared or if) near15 (substrate or wafer)	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_TDB	2004/08/01 19:21	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
19	BRS	L19	1270	(semiconductor or dopant) near3 (layer) near15 (radiat\$3 or infrared or if) near15 (substrate or wafer)	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/08/01 19:22	
20	BRS	L20	71	(semiconductor or dopant) near3 (layer) near15 (radiat\$3 or infrared or if) near15 (substrate or wafer) near20 (temperature)	USPAT; US-PG PUB; EPO; JPO; DERVENT; IBM_T DB	2004/08/01 19:22	

	U	1	Document ID	Title	Current OR	Pages
1	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20040092046 A1	Method of measuring a concentration of a material and method of measuring a concentration of a dopant of a semiconductor device	438/16	16
2	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20040023472 A1	Method for fabricating semiconductor device	438/542	13
3	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20030201515 A1	DC or AC electric field assisted anneal	257/530	26
4	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20030157415 A1	Apparatus and method for compensating critical dimension deviations across photomask	430/5	15
5	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20010026999 A1	DC or AC electric field assisted anneal	438/478	26
6	<input type="checkbox"/>	<input type="checkbox"/>	US 6645838 B1	Selective absorption process for forming an activated doped region in a semiconductor	438/530	11
7	<input type="checkbox"/>	<input type="checkbox"/>	US 6590219 B1	Apparatus and method for forming photoresist pattern with target critical dimension	250/492.2	15
8	<input type="checkbox"/>	<input type="checkbox"/>	US 6566016 B1	Apparatus and method for compensating critical dimension deviations across photomask	430/5	14

	U	1	Document ID	Title	Current OR	Pages
9	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 6552411 B2	DC or AC electric field assisted anneal	257/530	27
10	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 6380044 B1	High-speed semiconductor transistor and selective absorption process forming same	438/308	22
11	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 6274465 B1	DC electric field assisted anneal	438/510	21

	U	1	Document ID	Title	Current OR	Pages
12	<input type="checkbox"/>	<input type="checkbox"/>	US 6232207 B1	Doping process for producing homojunctions in semiconductor substrates	438/562	8
13	<input type="checkbox"/>	<input type="checkbox"/>	US 6078035 A	Integrated circuit processing utilizing microwave radiation	219/759	4
14	<input type="checkbox"/>	<input type="checkbox"/>	US 5959239 A	Thermovoltaic semiconductor device including a plasma filter	136/201	8
15	<input type="checkbox"/>	<input type="checkbox"/>	US 5422489 A	Light emitting device	250/488.1	8
16	<input type="checkbox"/>	<input type="checkbox"/>	US 3644770 A	PHOTOEMITTER HAVING A P-TYPE SEMICONDUCTIVE SUBSTRATE OVERLAID WITH CESIUM AND N-TYPE CESIUM OXIDE LAYERS	313/542	6
17	<input type="checkbox"/>	<input type="checkbox"/>	EP 1387396 A	Rapid thermal processing in semiconductor device production involves forming infrared-absorbing, dopant-containing semiconductor layer in semiconductor substrate, and exposure of substrate to infrared radiation		13

	U	1	Document ID	Title	Current OR	Pages
18	<input checked="" type="checkbox"/>	<input type="checkbox"/>	EP 416798 A	Mfr. of semiconductor silicon-on-insulation device - using rear side illumination with gate electrode as mask to cause dopant diffusion of source and drain regions		9